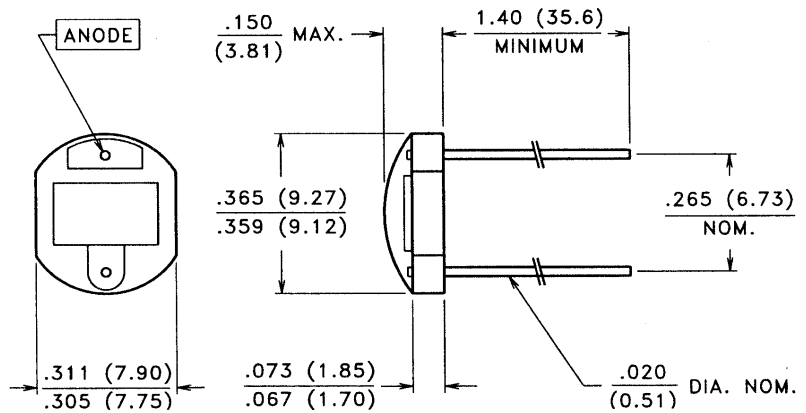




## PACKAGE DIMENSIONS inch (mm)



CASE 13 CERAMIC  
CHIP ACTIVE AREA: .026 in<sup>2</sup> (16.73 mm<sup>2</sup>)

## PRODUCT DESCRIPTION

Planar silicon photodiode mounted on a two lead ceramic substrate and coated with a thick layer of clear epoxy. These diodes exhibit low dark current under reverse bias and fast speed of response.

## ABSOLUTE MAXIMUM RATINGS

Storage Temperature: -20°C to 75°C  
Operating Temperature: -20°C to 75°C

**RoHS Compliant**



## ELECTRO-OPTICAL CHARACTERISTICS @ 25°C

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	VTD31AAH			UNITS
			Min.	Typ.	Max.	
$I_{SC}$	Short Circuit Current	H = 5 mW/cm <sup>2</sup> , 2850 K	150		225	μA
TC $I_{SC}$	$I_{SC}$ Temperature Coefficient	2850 K		.20		%/°C
$V_{OC}$	Open Circuit Voltage	H = 5 mW/cm <sup>2</sup> , 2850 K		350		mV
TC $V_{OC}$	$V_{OC}$ Temperature Coefficient	2850 K		-2.0		mV/°C
$I_D$	Dark Current	H = 0, $V_R$ = 15 V			50	nA
$C_J$	Junction Capacitance	H = 0, V = 0 V			500	pF
$S_R$	Sensitivity	@ Peak		.55		A/W
$\lambda_{range}$	Spectral Application Range		400		1150	nm
$\lambda_p$	Spectral Response - Peak			860		nm
$V_{BR}$	Breakdown Voltage		5			V
$\theta_{1/2}$	Angular Resp.-50% Resp. Pt.			±60		Degrees